

Ilesanmi Adesida

List of Publications by Year in descending order

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43
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docs citations

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times ranked

3610
citing authors

#	ARTICLE	IF	CITATIONS
1	Transfer printing by kinetic control of adhesion to an elastomeric stamp. <i>Nature Materials</i> , 2006, 5, 33-38.	27.5	1,348
2	Bendable GaN high electron mobility transistors on plastic substrates. <i>Journal of Applied Physics</i> , 2006, 100, 124507.	2.5	157
3	In-plane bandgap control in porous GaN through electroless wet chemical etching. <i>Applied Physics Letters</i> , 2002, 80, 980-982.	3.3	102
4	Differences in the reaction kinetics and contact formation mechanisms of annealed Ti ^{Al} Mo ^{Au} Ohmic contacts on n-GaN and AlGa ^N GaN epilayers. <i>Journal of Applied Physics</i> , 2007, 101, 013702.	2.5	91
5	Comparative study of Ti ^{Al} Mo ^{Au} , Mo ^{Al} Mo ^{Au} , and V ^{Al} Mo ^{Au} ohmic contacts to AlGa ^N GaN heterostructures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004, 22, 2409.	1.6	88
6	Printed Arrays of Aligned GaAs Wires for Flexible Transistors, Diodes, and Circuits on Plastic Substrates. <i>Small</i> , 2006, 2, 1330-1334.	10.0	76
7	Properties of R.F. magnetron sputtered cadmium ^{tin} oxide and indium ^{tin} oxide thin films. <i>Thin Solid Films</i> , 2005, 479, 223-231.	1.8	74
8	Surface-state origin for the blueshifted emission in anodically etched porous silicon carbide. <i>Journal of Applied Physics</i> , 2004, 95, 490-496.	2.5	73
9	Bendable GaAs metal-semiconductor field-effect transistors formed with printed GaAs wire arrays on plastic substrates. <i>Applied Physics Letters</i> , 2005, 87, 083501.	3.3	70
10	Gigahertz operation in flexible transistors on plastic substrates. <i>Applied Physics Letters</i> , 2006, 88, 183509.	3.3	67
11	Formation mechanism of Ohmic contacts on AlGa ^N GaN heterostructure: Electrical and microstructural characterizations. <i>Journal of Applied Physics</i> , 2008, 103, .	2.5	66
12	Structural and spectroscopic characterization of porous silicon carbide formed by Pt-assisted electroless chemical etching. <i>Solid State Communications</i> , 2003, 126, 245-250.	1.9	65
13	Dislocation-induced nonuniform interfacial reactions of Ti ^{Al} Mo ^{Au} ohmic contacts on AlGa ^N GaN heterostructure. <i>Applied Physics Letters</i> , 2005, 87, 141915.	3.3	65
14	Morphology and luminescence of porous GaN generated via Pt-assisted electroless etching. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 2375.	1.6	52
15	The role of barrier layer on Ohmic performance of Ti ^{Al} -based contact metallizations on AlGa ^N GaN heterostructures. <i>Journal of Applied Physics</i> , 2006, 100, 023708.	2.5	47
16	Monte Carlo simulation of ion beam penetration in solids. <i>Radiation Effects</i> , 1982, 61, 223-233.	0.4	46
17	Morphology evolution and luminescence properties of porous GaN generated via Pt-assisted electroless etching of hydride vapor phase epitaxy GaN on sapphire. <i>Journal of Applied Physics</i> , 2003, 94, 7526.	2.5	44
18	Ion bombardment of resists. <i>Nuclear Instruments & Methods in Physics Research</i> , 1983, 209-210, 79-86.	0.9	43

#	ARTICLE	IF	CITATIONS
19	A photon detector with very high gain at low bias and at room temperature. Applied Physics Letters, 2007, 91, 171112.	3.3	37
20	Direct contact mechanism of Ohmic metallization to AlGaIn/GaN heterostructures via Ohmic area recess etching. Applied Physics Letters, 2009, 95, .	3.3	37
21	Sub-Poissonian shot noise of a high internal gain injection photon detector. Optics Express, 2008, 16, 12701.	3.4	34
22	Anatomy-performance correlation in Ti-based contact metallizations on AlGaIn/GaN heterostructures. Journal of Applied Physics, 2007, 101, 033708.	2.5	33
23	Ultralow resistance Si-containing Ti/Al/Mo/Au Ohmic contacts with large processing window for AlGaIn/GaN heterostructures. Applied Physics Letters, 2006, 88, 212107.	3.3	28
24	Characterization of Au and Al segregation layer in post-annealed thin Ti/Al/Mo/Au Ohmic contacts to n-GaN. Journal of Applied Physics, 2005, 98, 106105.	2.5	27
25	Etching characteristics of Al _x Ga _{1-x} As in (NH ₄) ₂ Sx solutions. Applied Physics Letters, 1992, 60, 1114-1116.	3.3	24
26	Noninterfacial-nitride formation ohmic contact mechanism in Si-containing Ti/Al/Mo/Au metallizations on AlGaIn/GaN heterostructures. Applied Physics Letters, 2005, 87, 262111.	3.3	20
27	Ti/Al/Mo/Au Ohmic contacts to all-binary AlN/GaN high electron mobility transistors. Applied Physics Letters, 2008, 93, .	3.3	20
28	The range of light ions in polymeric resists. Journal of Applied Physics, 1984, 56, 1801-1807.	2.5	17
29	Ohmic contacts to n-GaN capped AlGaIn/AlN/GaN high electron mobility transistors. Applied Physics Letters, 2007, 91, .	3.3	15
30	Accumulation of fluorine in CF ₄ plasma-treated AlGaIn/GaN heterostructure interface: An experimental investigation. Journal of Applied Physics, 2009, 105, .	2.5	15
31	Study of fluorine bombardment on the electrical properties of AlGaIn/GaN heterostructures. Journal of Vacuum Science & Technology B, 2007, 25, 2607.	1.3	14
32	Breakdown Voltage Enhancement of AlGaIn/GaN High-Electron-Mobility Transistors via Selective-Area Growth for Ohmic Contacts over Ion Implantation. Journal of Electronic Materials, 2010, 39, 499-503.	2.2	14
33	Low resistance Mo/Al/Mo/Au ohmic contact scheme to InAlN/AlN/GaN heterostructure. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1538-1540.	1.8	14
34	Fabrication of nanowires with high aspect ratios utilized by dry etching with SF ₆ :C ₄ F ₈ and self-limiting thermal oxidation on Si substrate. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 763-768.	1.2	13
35	Fine line lithography using ion beams. Nuclear Instruments & Methods in Physics Research B, 1985, 7-8, 923-928.	1.4	12
36	Recessed 70-nm Gate-Length AlGaIn/GaN HEMTs Fabricated Using an Al ₂ O ₃ /SiN _x Dielectric Layer. IEEE Electron Device Letters, 2009, 30, 913-915.	3.9	9

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37	InGaAs metal-semiconductor-metal photodetectors with a hybrid combination of transparent and opaque electrodes. Applied Physics Letters, 1997, 70, 3026-3028.	3.3	8
38	Comparative study of self-aligned and nonself-aligned SiGe p-metal-oxide-semiconductor modulation-doped field effect transistors with nanometer gate lengths. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 3488.	1.6	5
39	<title>Long-wavelength metal-semiconductor-metal photodetectors with transparent and opaque electrodes</title>. , 1995, , .		4
40	Elevated-Temperature Annealing Effects on AlGaIn/GaN Heterostructures. Journal of Electronic Materials, 2011, 40, 2344-2347.	2.2	3
41	Process development for the realization of thermally-reliable enhancement-mode InAlAs/InGaAs/InP HEMTs with excellent DC and RF performance. , 2006, , .		1
42	Monolithic integration of thermally stable enhancement-mode and depletion-mode InAlAs/InGaAs/InP HEMTs utilizing Ir-gate and Ag-ohmic contact technologies. , 2006, , .		0
43	Nanometer-scale gaps in hydrogen silsesquioxane resist for T-gate fabrication. Journal of Vacuum Science & Technology B, 2007, 25, 2081.	1.3	0